

KS54AHCT 238
KS74AHCTT-67-21-55
3-Line 8-Line Decoders/Demultiplexers**FEATURES**

- Designed specifically for high-speed memory decoders and data transmission systems.
- Incorporates 2 enable inputs to simplify cascading and/or data reception
- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- High-Drive-Current outputs:
- $I_{OL} = 8 \text{ mA} @ V_{OL} = 0.5V$
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over Industrial and military temperature ranges:
KS74AHCT: -40°C to +85°C
KS54AHCT: -55°C to +125°C
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

DESCRIPTION

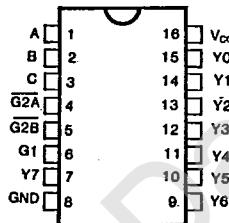
These devices are designed to be used in high-performance memory-decoding or data-routing applications requiring very short propagation delay times. In high-performance memory systems, these decoders can be used with high-speed memories utilizing a fast enable circuit, the delay times of these decoders and the enable time of the memory are usually less than the typical access time of the memory. This means that the effective system delay introduced by the decoder is negligible.

This conditions at the binary select inputs and the three enable inputs select one of eight input lines. Two active-low and one active-high enable inputs reduce the need for external gates or inverters when expanding.

A 24-line decoder can be implemented without external inverters and a 31-line decoder requires only one inverter. An enable input can be used as a data input for demultiplexing applications.

These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to Vcc and ground.

PIN CONFIGURATION**FUNCTION TABLE**

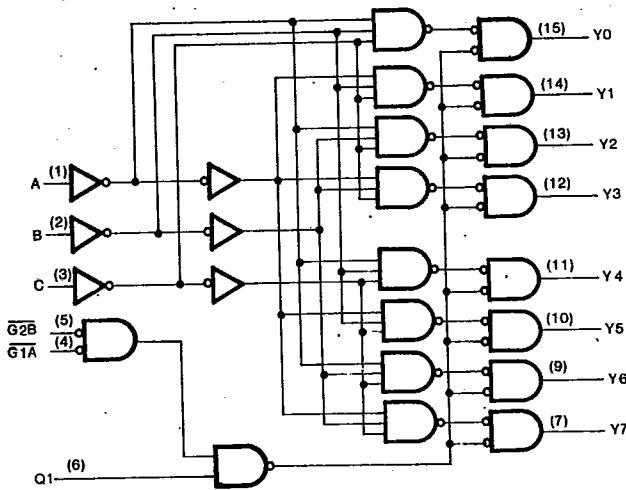
		Enable Inputs			Select Inputs			Outputs							
G1	̄G2*	C	B	A	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7			
X	H	X	X	X	L	L	L	L	L	L	L	L			
L	X	X	X	X	L	L	L	L	L	L	L	L			
H	L	L	L	L	H	L	L	L	L	L	L	L			
H	L	L	L	H	L	H	L	L	L	L	L	L			
H	L	L	H	L	L	L	H	L	L	L	L	L			
H	L	H	L	L	L	L	L	H	L	L	L	L			
H	L	H	L	H	L	L	L	L	L	H	L	L			
H	L	H	H	L	L	L	L	L	L	L	H	L			
H	L	H	H	H	L	L	L	L	L	L	L	H			

* $\bar{G}2 = \bar{G}2A + \bar{G}2B$ 

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T-67-21-55

LOGIC DIAGRAM



Absolute Maximum Ratings*

Supply Voltage Range V_{CC}, -0.5V to +7V
DC Input Diode Current, I_{IK}

(V_I < -0.5V or V_I > V_{CC} + 0.5V) ±20 mA
DC Output Diode Current, I_{OK}

(V_O < -0.5V or V_O > V_{CC} + 0.5V) ±20 mA
Continuous Output Current Per Pin, I_O

(-0.5V < V_O < V_{CC} + 0.5V) ±35 mA
Continuous Current Through

V_{CC} or GND pins ±125 mA
Storage Temperature Range, T_{STG} -65°C to +150°C

Power Dissipation Per Package, P_D^t 500 mW

* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

^t Power Dissipation temperature derating:
Plastic Package (N): -12mW/°C from 65°C to 85°C
Ceramic Package (J): -12mW/°C from 100°C to 125°C

Recommended Operating Conditions

Supply Voltage, V_{CC} 4.5V to 5.5V

DC Input & Output Voltages*, V_{IN}, V_{OUT} 0V to V_{CC}

Operating Temperature

Range	KS74AHCT: -40°C to +85°C
	KS54AHCT: -55°C to +125°C

Input Rise & Fall Times, t_R, t_F Max 500 ns

* Unused inputs must always be tied to an appropriate logic voltage level (either V_{CC} or GND)



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DC ELECTRICAL CHARACTERISTICS ($V_{CC}=5V \pm 10\%$ Unless Otherwise Specified)

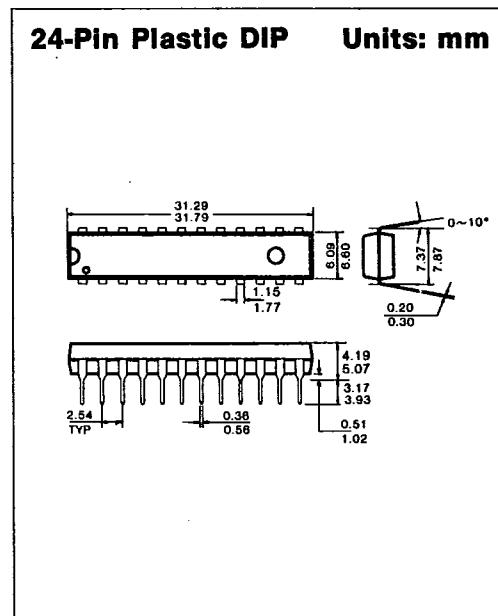
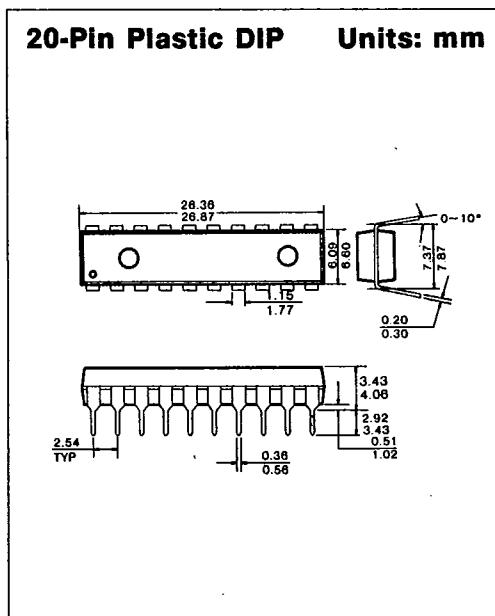
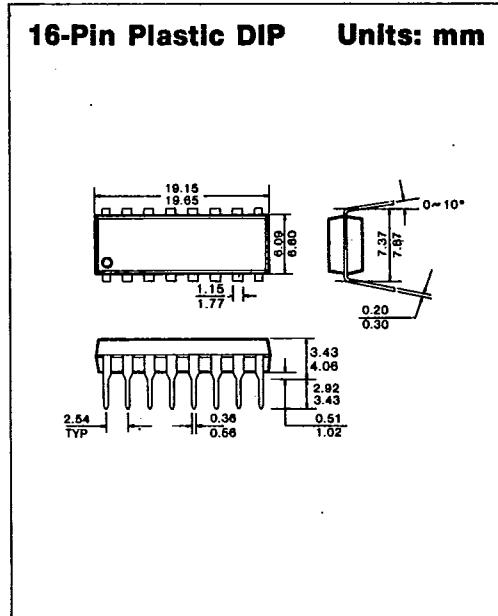
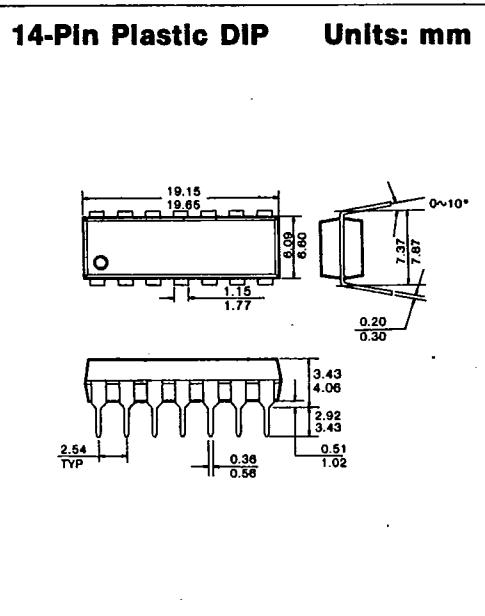
Characteristic	Symbol	Test Conditions	$T_A=25^\circ C$		$KS74AHCT$	$KS54AHCT$	Unit
			Typ		$T_A=-40^\circ C$ to $+85^\circ C$	$T_A=-55^\circ C$ to $+125^\circ C$	
Minimum High-Level Input Voltage	V_{IH}			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	V_{IL}			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V_{OH}	$V_{IN}=V_{IH}$ or V_{IL} $I_o=-20\mu A$ $I_o=-4mA$	V_{CC} 4.2	$V_{CC}-0.1$ 3.98	$V_{CC}-0.1$ 3.84	$V_{CC}-0.1$ 3.7	V
Maximum Low-Level Output Voltage	V_{OL}	$V_{IN}=V_{IH}$ or V_{IL} $I_o=20\mu A$ $I_o=4mA$ $I_o=8mA$	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	I_{IN}	$V_{IN}=V_{CC}$ or GND		± 0.1	± 1.0	± 1.0	μA
Maximum Quiescent Supply Current	I_{CC}	$V_{IN}=V_{CC}$ or GND $I_{OUT}=0\mu A$		8.0	80.0	160.0	μA
Additional Worst Case Supply Current	ΔI_{CC}	per input pin $V_I=2.4V$ other Inputs: at V_{CC} or GND $I_{OUT}=0\mu A$		2.7	2.9	3.0	mA

AC ELECTRICAL CHARACTERISTICS (Input t_r , $t_f \leq 2$ ns), AHCT238

Characteristic	Symbol	Conditions ^t	$KS74AHCT$		$KS54AHCT$		Unit
			$T_A=25^\circ C$ $V_{CC}=5.0V$	$T_A=-40^\circ C$ to $+85^\circ C$ $V_{CC}=5.0V \pm 10\%$	$T_A=-55^\circ C$ to $+125^\circ C$ $V_{CC}=5.0V \pm 10\%$	Min	
Propagation Delay, A, B, C or Y	t_{PLH}	$C_L=50pF$	12		20		ns
	t_{PHL}		12		20		
Propagation Delay, G1 to any Y	t_{PLH}	$C_L=50pF$	10		17		ns
	t_{PHL}		10		17		
Propagation Delay, G2A or G2B to any Y	t_{PLH}	$C_L=50pF$	10		17		ns
	t_{PHL}		10		17		
Input Capacitance	C_{IN}		5				pF
Power Dissipation Capacitance*	C_{PD}		50				pF

* C_{PD} determines the no-load dynamic power dissipation: $P_D=C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.^t For AC switching test circuits and timing waveforms see section 2.

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PACKAGE DIMENSIONST-90-20**1. PLASTIC PACKAGES**

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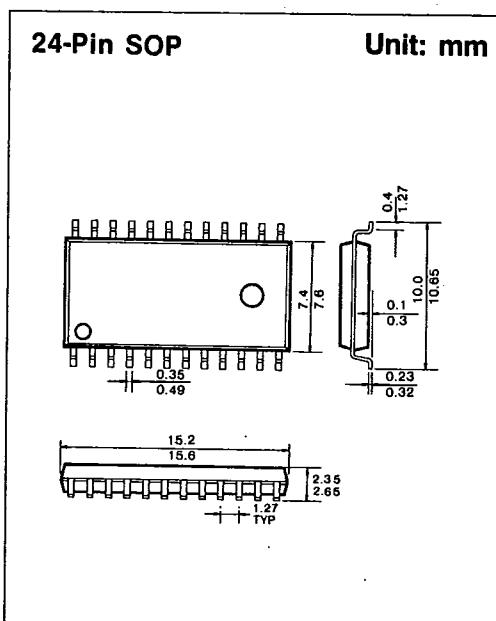
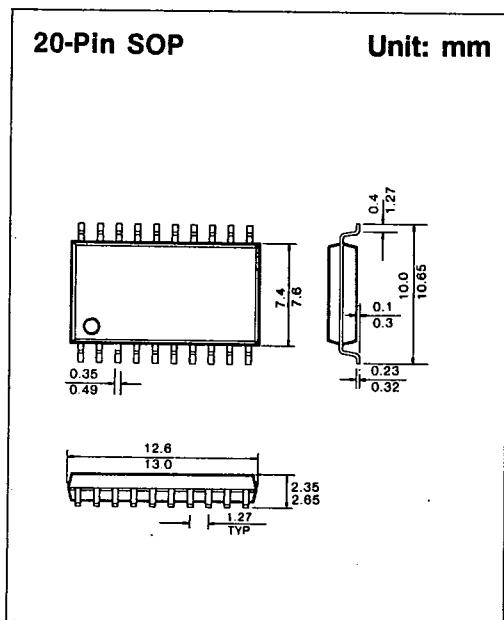
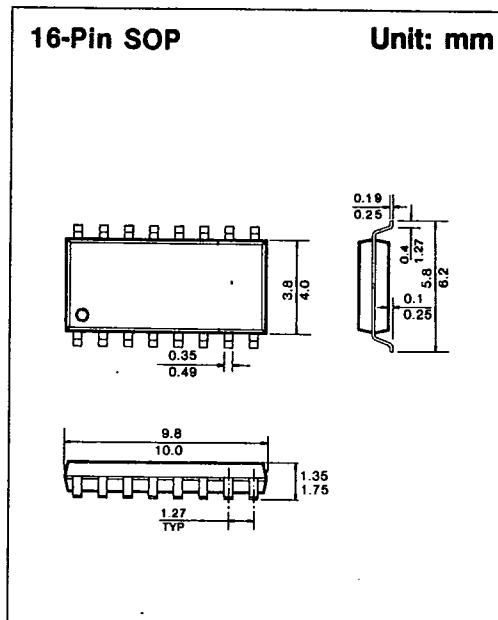
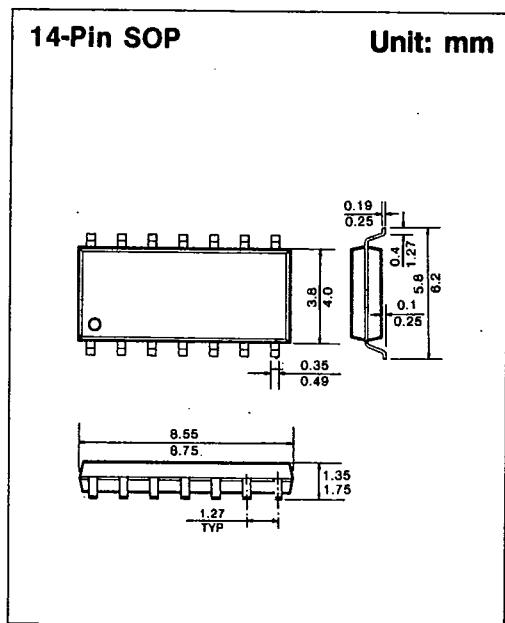


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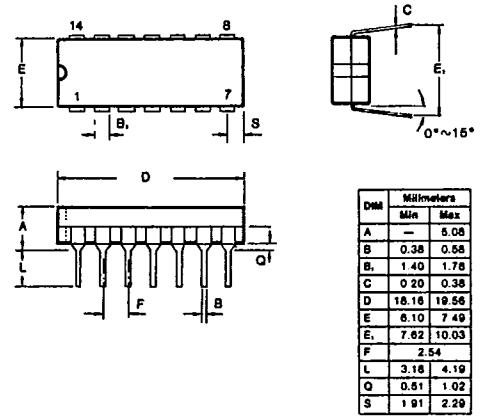
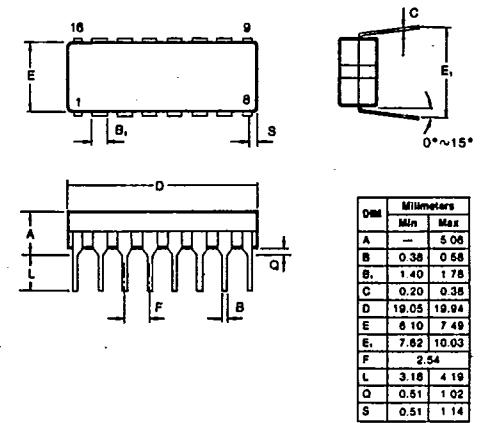
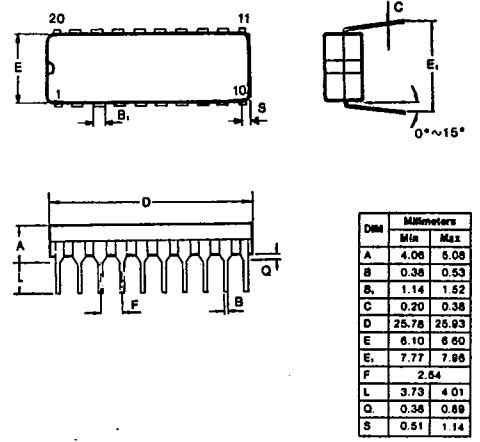
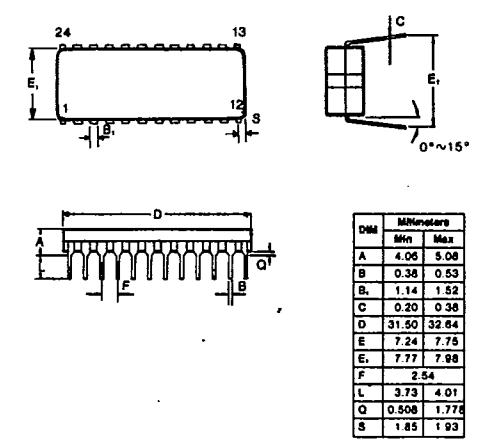
PACKAGE DIMENSIONS**T-90-20**

SAMSUNG SEMICONDUCTOR

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PACKAGE DIMENSIONST-90-20**2. CERAMIC PACKAGES****14-Pin Ceramic DIP Units: mm****16-Pin Ceramic DIP Units: mm****20-Pin Ceramic DIP Units: mm****24-Pin Ceramic DIP Units: mm**

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